



Small Signal Schottky Diode

Features

- For general purpose applications
- This diode features low turn-on voltage.
 The devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.



- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications
- This diode is also available in a DO-35 case with type designation BAT86.
- AEC-Q101 qualified
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



Mechanical Data

Case: MiniMELF SOD-80
Weight: approx. 31 mg
Packaging codes/options:

GS18/10 k per 13" reel (8 mm tape), 10 k/box GS08/2.5 k per 7" reel (8 mm tape), 12.5 k/box

Applications

Applications where a very low forward voltage is required

Parts Table

Part	Ordering code	Marking	Remarks
BAS86	BAS86-GS18 or BAS86-GS08		Tape and Reel

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

and ,	•			
Parameter	Test condition	Symbol	Value	Unit
Continuous reverse voltage		V_R	50	V
Forward continuous current		l _F	200 ¹⁾	mA
Repetitive peak forward current	$t_p < 1 \text{ s, } v \le 0.5$	I _{FRM}	500 ¹⁾	mA
Power dissipation ¹⁾		P _{tot}	200 ¹⁾	mW

¹⁾ Valid provided that electrodes are kept at ambient temperature

Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R _{thJA}	300 ¹⁾	K/W
Junction temperature		Tj	125	°C
Ambient operating temperature range		T _{amb}	- 65 to + 125	°C
Storage temperature range		T _S	- 65 to +150	°C

¹⁾ Valid provided that electrodes are kept at ambient temperature

Vishay Semiconductors

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified



Parameter	Test condition	Symbol	Min.	Тур.	Max.	Unit
Reverse breakdown voltage	I _R = 10 μA (pulsed)	V _(BR)	50			V
Leakage current	V _R = 40 V	I _R			5	μΑ
Forward voltage	Pulse test $t_p < 300 \mu s$, $I_F = 0.1 \text{ mA}$, $\delta < 2 \%$	V _F		200	300	mV
	Pulse test $t_p < 300 \mu s$, $I_F = 1 \text{ mA}, \delta < 2 \%$	V _F		275	380	mV
	Pulse test $t_p < 300 \ \mu s$, $I_F = 10 \ mA$, $\delta < 2 \ \%$	V _F		365	450	mV
	Pulse test $t_p < 300 \ \mu s$, $I_F = 30 \ mA$, $\delta < 2 \ \%$	V _F		460	600	mV
	Pulse test $t_p < 300 \mu s$, $I_F = 100 \text{ mA}$, $\delta < 2 \%$	V _F		700	900	mV
Diode capacitance	V _R = 1 V, f = 1 MHz	C _D			8	pF
Reverse recovery time	$I_F = 10 \text{ mA}, I_R = 10 \text{ mA},$ $I_{rr} = 1 \text{ mA},$	t _{rr}			5	ns

Typical Characteristics

T_{amb} = 25 °C, unless otherwise specified

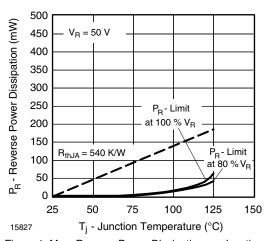


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

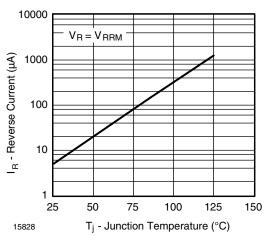


Figure 2. Reverse Current vs. Junction Temperature

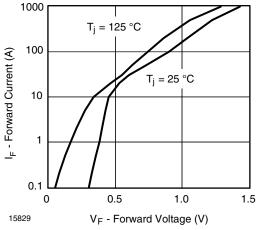


Figure 3. Forward Current vs. Forward Voltage

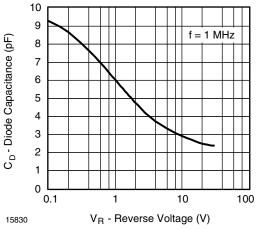
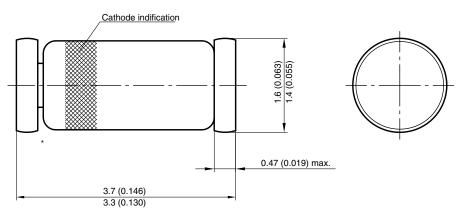


Figure 4. Diode Capacitance vs. Reverse Voltage



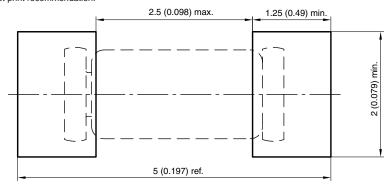
Vishay Semiconductors

Package Dimensions in millimeters (inches): MiniMELF SOD-80



^{*} The gap between plug and glass can be either on cathode or anode side

Foot print recommendation:



Document no.:6.560-5005.01-4 Rev. 8 - Date: 07.June.2006

96 12070



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08

www.vishay.com